## N on Arrhenius Behavior of Surface Di usion Near a Phase Transition Boundary

I. Vattulainen,<sup>1;2</sup> J. Merikoski,<sup>1;2;3</sup> T. A la-N issila,<sup>1;2;4</sup> and S.C. Ying<sup>2</sup>

<sup>1</sup>Helsinki Institute of Physics, P.O. Box 9 (Siltavuorenpenger 20 C), FIN (00014 University of Helsinki, Finland

<sup>2</sup>Department of Physics, Box 1843, Brown University, Providence, R.I. 02912, U.S.A.

<sup>3</sup>Department of Physics, University of Jyvaskyla, P.O. Box 35, FIN {40351 Jyvaskyla, Finland

<sup>4</sup>Laboratory of Physics, Tam pere University of Technology, P.O. Box 692, FIN {33101 Tam pere, Finland

(M arch 23, 2024)

We study the non-A mhenius behavior of surface di usion near the second-order phase transition boundary of an adsorbate layer. In contrast to expectations based on m acroscopic therm odynamic e ects, we show that this behavior can be related to the average m icroscopic jump rate which in turn is determined by the waiting-time distribution W (t) of single-particle jumps at short times. At long times, W (t) yields a barrier that corresponds to the rate-limiting step in di usion. The m icroscopic information in W (t) should be accessible by STM m easurements.

PACS numbers: 68.35 Fx, 82.20 Pm

The migration of atoms and molecules is one of the most important processes taking place on solid surfaces. It appears in many phenomena such as catalytic reactions and surface grow th that are in portant for practical applications [1]. In most experimental and theoretical studies of the surface di usion constant D , its tem perature dependence is analyzed through an assumed Arrhenius form, where D is written as a product of an entropic prefactor D<sub>0</sub> and a term exp(  $E_{a}^{D} = k_{B}T$ ) describing therm ally activated jum ps over an energy barrier  $E_{A}^{D}$ . Although the Arrhenius form can be derived from m icroscopic considerations in som e special cases [2,3], a rigorous justi cation for its use in interacting systems at nite coverages is not available. Further, even in the cases where D appears to have an Arrhenius tem perature dependence over a nite tem perature range, its m icroscopic interpretation may not always be clear. This is because for an interacting system, there m ay be m any m icroscopic activation barriers. Thus the value of the measured e ective di usion barrier E must result from som e com plex average of all of them , and does not refer to any m icroscopic process in particular [4].

In fact, the values for  $D_0$  and  $E_{\lambda}^{D}$  can be strongly temperature-dependent indicating a region of non-Arrhenius behavior. This becom esespecially pronounced near surface phase transition boundaries, where rapid variations of D have been observed in experiments [4[6] and computer simulations [2,7]. Such rapid changes are often accompanied by the well-known \compensation" effect [8], where an apparent increase in  $E_{A}^{D}$  is compensated by an increase in the prefactor D $_0$  [6]. How ever, in most cases the underlying reasons for non-Arrhenius behavior are not understood. It is the purpose of the present work to study these issues near a second-order phase transition in a surface adsorbate layer. We show that in contrast to the comm on folk love that an anom alous tem perature dependence in D near T<sub>c</sub> would be predom inantly due to non-local therm odynam ic e ects, it can be explained by the m icroscopic single-particle jump rate . This quantity is determined by the short-time behavior of the waiting-time distribution W (t) for single-particle jumps. Moreover, we show that for long times, W (t) yields an elective activation barrier that corresponds to the rate-limiting step in di usion. Thus W (t) provides a connection between m icroscopic and m acroscopic aspects of di usion. Further, it is experimentally available through e.g. STM m easurements [9].

In this Letter, we have carried out M onte C arlo (M C) simulations for a model of oxygen on the W (110) surface [10,11]. In this system, the substrate remains unreconstructed [12], the oxygen atom s have well-de ned adsorption sites [13], and desorption of oxygen occurs only at tem peratures 1600 K or above [12]. Therefore, this system is very suitable for simulation studies using a latticegas description. We use the lattice-gasm odel constructed by Sahu et al. [11] to describe the main features of the phase diagram . The Ham iltonian includes pair interactions up to fth nearest neighbors and som e three-body interactions [11], the attractive ones being the dom inant. W e concentrate on results for the coverage = 0.45 over a wide tem perature range. For this coverage at a low tem perature, the adlayer is in the ordered p (2 1) phase, 710 K it undergoes a second-order tranwhile at  $T_c$ sition [11] to a disordered phase [14]. For details of the model and MC simulations, see Refs. [10,15].

O ur simulation results for the tracer and collective diffusion coe cients D<sub>T</sub> and D<sub>C</sub> (for de nitions see e.g. Ref. [4]), respectively, are given in Fig.1. We rst note that their qualitative behavior is similar and that the e ective di usion barrier  $F_{H}^{2}$  de ned as

$$E_{A}^{D} \qquad \frac{\varrho (\log D)}{\varrho (1=k_{B}T)}$$
(1)

is approximately constant at low and high temperatures away from  $T_c$ . This implies that the dision constants obey simple Arrhenius behavior. Near  $T_c$ , however, the

tem perature dependence of the di usion constants is strongly non-Arrhenius.

In the G reen-K ubo form alism [4], the expression for D<sub>c</sub> contains a therm odynamic factor inversely proportional to the compressibility, which is governed by the global number uctuations of the adlayer. It is offen assumed that a possible non-A rrhenius behavior of D<sub>c</sub> near the phase transition boundary is predominantly due to the critical behaviour of this factor [7]. We show below that this is not the case here: The non-A rrhenius behavior of both D<sub>T</sub> and D<sub>c</sub> has a dynamic origin and can be traced back to the temperature dependence of the local single-particle jump rate . To demonstrate this, we show in Fig.1 the temperature dependence of and

as well as that of  $\mathsf{D}_{\mathsf{T}}\,$  and  $\mathsf{D}_{\mathsf{C}}$  . It can be seen from Fig. 1 that while the di usion constants have a turning point and sharp temperature variations close to  $T_{c}$ , the therm odynam ic factor has only a relatively weak tem perature dependence in this region and cannot account for the non-Arrhenius behavior of the di usion constants. On the other hand, the single-particle jump rate has exactly the same behavior near  $T_c$  as  $D_T$  and  $D_c$ . These observations can be understood theoretically within the dynamical mean eld theory (DMF) [16], which yields D<sub>T</sub> / and D\_c  $\,$  / . W e can conclude that the strong tem perature dependence of both D $_{\rm T}$  and D $_{\rm C}$  near T $_{\rm c}$  is indeed of the same dynamic origin, coming from the average single-particle transition rate .

We next focus on the elective di usion barrier  $\mathbf{F}$  as extracted from Eq. (1) for  $D_T$  . As shown by squares in Fig. 2,  $E_A^D$  has a sharp peak near  $T_c$ . This peak in  $E_A^D$ is accompanied by a strong increase in the value of the corresponding prefactor  $D_0$  shown in the inset of Fig.2. This is yet another example of the well-known compensation e ect [4,8]. Here the compensation simply results from the fact that when the tem perature dependence is non-Arrhenius, there is no unique way of separating the prefactor and the barrier contributions. Since the tem perature dependence of the di usion constant itself near T<sub>c</sub> is smooth and nonsingular, any dram atic change in the tem perature dependence of the e  $\mbox{ ective barrier } E^D_{\tt a}$ must be followed by a corresponding change in the e ective prefactor D  $_0$ . We note that the same phenom enon occurs for collective di usion as well.

To understand the observed strong tem perature variation of  $E_A^D$  near  $T_c$ , we need to consider the energetics of the m icroscopic jump processes which determ ine the average jump rate . At nite coverages, there is a very com plex distribution P ( $E_a$ ) for the instantaneous activation barriers  $E_a$  [17] which an adatom needs to overcom e in a jump attempt from one con guration to another. At high T, P ( $E_a$ ) is strongly peaked at sm all values of  $E_a$ , while at low tem peratures the situation is com pletely the opposite [18]. The change in the distribution takes place around  $T_c$ , thus characterizing the ordering of the adlayer as the tem perature is decreased below  $T_c$ . This change in tum results in a strong temperature dependence of the average transition rate around  $T_c$ , as shown in Fig. 1. We point out that the instantaneous activation barriers  $E_a$  cannot explain the peak of the elective barrier  $E_A^D$  in Fig. 2, since the largest value of  $E_a$  in our model system is only about 0.4 eV [18]. Thus, the peak does not refer to any microscopic rate-limiting process. Instead, it arises from an entropic contribution [19] to which has a strong temperature dependence in the vicinity of  $T_c$ .

To gain more insight into the microscopic dynamical processes and the anomalous temperature dependence near  $T_c$ , we next introduce the waiting-time distribution W (t) of single-particle jumps [20]. Suppose a single particle (in the presence of other particles) had performed its last transition at time t = 0. Then W (t) is the probability density that the particle in question performs its next transition at time t after it remained still until t. Here the most practical de nition of \time" in the MC simulations is to consider the time scale as the number of jump attempts of the particle, denoted by n. Then the waiting-time distribution is simply W (n). This provides a direct connection with the dynam ic jump rate discussed above via

hni 
$$\frac{1}{m} = \sum_{n=1}^{X^{1}} n W(n);$$
 (2)

where hni is the average waiting-tim e of the particle.

At very long times, we expect W (t) to decay as W (t) exp (t=). Here the characteristic time describes the longest time scale among the various m icroscopic processes, which constitutes the rate-lim iting factor form ass transport. This expected exponential decay at long times is indeed observed for ourm odel system, as dem onstrated in Fig. 3. We can then de ne an e ective activation barrier  $E_A^W$  via by considering the jump probability  $p = 1 = p_0 \exp(E_A^W = k_B T)$ . As shown by circles in Fig. 2, the activation barrier  $E_A^W$  extracted from the asymptotic region of W (t) decreases monotonically with increasing tem perature, and agrees with the e ective diffusion barrier E A extracted from an Arrhenius analysis of D<sub>T</sub> far from T<sub>c</sub>. Additional studies in our model system [18] indicate that the value of  $E_A^W$  is closely related to the instantaneous activation barrier characterizing the dom inant m icroscopic processes. In ourm odel the m icroscopic barriers have a maximum value of about 0.4 eV and thus the barrier  $\mathbf{E}_{\mathbf{A}}^{\mathsf{W}}$  does not have the sharp peak displayed by the e ective di usion barrier  $\mathbb{P}$ .

It turns out that the tem perature dependence of the barrier  $E_A^D$  results mainly from the short-time behavior of W (n). This is demonstrated by dividing the sum in Eq. (2) into two parts, the rst of which is the short-time contribution  $\operatorname{Im}_S = \prod_{n=1}^{n_{co}} nW(n)$ . This quantity accounts for the contribution up to a crossover time  $n_{co}$ , which separates the short-time regime from the asymptotic exponential decay. W hat remains is the long-time

contribution  $\operatorname{hni}_{L} = \operatorname{hni} \operatorname{hni}_{S}$ . As expected, from Fig.4 we observe that the short-time regime gives the dom inant contribution to further, the short-time regime of W (n) is strongly a ected by the critical uctuations, being mainly responsible for the anom alous temperature dependence of the di usion constants near  $T_{c}$ .

To sum m arize, within the present m odel of 0/W (110), the non-Arrhenius behavior near  $T_{\rm c}$  was found to have a mainly dynamic origin, rejecting the dependence of the single-particle jump rate on the critical uctuations close to  $T_{\rm c}$ . Surprisingly, in our studies the therm odynam ic factor gives only a m inor contribution to the tem perature dependence of the collective di usion constant D $_{\rm C}$ , and the anom alous tem perature dependence for both D $_{\rm T}$  and D $_{\rm C}$  results from the dynam ic factor

. We nd that the single-particle waiting-time distribution W (t) gives the most detailed picture of the microscopic processes. It has been recently dem onstrated by Swartzentruber [9] that this distribution function in the presence of several di erent microscopic activation barriers can indeed be measured using the STM . From the long-time tail of W (t) one can obtain information on the energetics of the rate-lim iting processes of di usion in the form of an e ective activation barrier  $E^W_A$  . On the other hand, the tem perature variation of the e ective di usion barrier  $E_{A}^{D}$  directly re ects that of the microscopic jump rate , and depends not only on the long-time tail of W (t) but also on its short-time behavior. In the shorttime regime near  $T_c$ , W (t) is strongly a ected by the critical uctuations. The uctuations there lead to a strong tem perature dependence of the transition entropy and an additional contribution to the e ective barrier  $E^D_{a}$ .

I.V. thanks the N este Co. Foundation and the Jenny and AnttiW ihuriFoundation.J.M. is supported by the F innish CulturalFoundation.This research has also been partially supported by a grant from the o  $\infty$  of N aval R esearch (S.C.Y. and J.M.) and by the A cadem y of F inland (J.M. and T.A. N.). Finally, com puting resources of the University of Helsinkiare gratefully acknow ledged.

- [L] V.T.Binh (editor), Surface M obilities on Solid M aterials: Fundam ental Concepts and Applications (P lenum Press, New York, 1981); M.G.Lagally (editor), K inetics of Ordering and G rowth at Surfaces (P lenum Press, New York, 1990).
- [2] T. A la-N issila and S. C. Y ing, Prog. Surf. Sci. 39, 227 (1992).
- [3] L.Y. Chen and S.C. Ying, Phys. Rev. B 49, 13838 (1994).
- [4] R.Gomer, Rep. Prog. Phys. 53, 917 (1990).
- [5] A.G. Naum ovets and Yu.S. Vedula, Surf. Sci. Rep. 4, 365 (1985).

- [6] V.P.Zhdanov, Surf. Sci.Rep. 12, 183 (1991).
- [7] A. Sadiq and K. Binder, Surf. Sci. 128, 350 (1983); A.
   V. M yshlyavtsev, A. A. Stepanov, C. Uebing, and V. P.
   Zhdanov, Phys. Rev. B 52, 5977 (1995); C. Uebing and
   R. Gomer, Surf. Sci. 331-333, 930 (1995).
- [8] Von W . M eyer and H. Neldel, Z. Tech. Phys. 12, 588 (1937).
- [9] B. S. Swartzentruber, Phys. Rev. Lett. 76, 459 (1996);
   Surf. Sci. 374, 277 (1997).
- [10] I. Vattulainen, J. Merikoski, T. Ala-Nissila, and S. C. Ying, Surf. Sci. 366, L697 (1996).
- [11] D. Sahu, S.C. Ying, and J.M. Kosterlitz, in The Structure of Surfaces II, edited by J.F. van der Veen and M. A. van Hove (Springer-Verlag, Berlin, 1988) p. 470.
- [12] C.R.Brundle and J.Q.Broughton, Chapter 3 in Volum e 3A of The Chem ical Physics of Solid Surfaces and Heterogeneous Catalysis: Chem isorption System s, edited by D.A.King and D.P.W oodru (Elsevier, Amsterdam, 1990); and references therein.
- [13] A. Elbe, G. Meister, and A. Goldmann, Surf. Sci. 371, 438 (1997); and references therein.
- [14] G.-C. W ang, T.-M. Lu, and M. G. Lagally, J. Chem. Phys. 69, 479 (1978).
- [15] I. Vattulainen, J. Merikoski, T. A la-Nissila, and S. C. Ying, in Proceedings of \Surface Di usion: Atom istic and Collective Processes", edited by M. C. Tringides (Plenum Press, New York, 1997).
- [16] T.H jelt, I.Vattulainen, J.M erikoski, T.A la-N issila, and S.C.Ying, to appear in Surface Science Letters (1997); cond-m at/9702233.
- [17] In our M C studies, we used the so called TDA algorithm [10]. In this ethod, the transition of an adatom from the initial state with energy  $E_i$  to the nal state with energy  $E_f$  proceeds by two successive steps via the interm ediate state with energy  $E_I$ . For  $E_I$ , we used the form  $E_I =$  $(E_i + E_f)=2 +$ , where characterizes the activation barrier in the zero coverage limit due to the substrateadatom interaction. The instantaneous activation barrier  $E_a$  for a jump attempt from a led to a vacant site is then  $E_a = \max (E_I - E_i; E_f - E_i; 0)$ : For further details and for the choice of , see Refs. [10,15].
- [18] I. Vattulainen, J. Merikoski, T. Ala-Nissila, and S. C. Ying, in preparation (1997).
- [19] W ithin the fram ework of the Transition State Theory
  P. Hanggi, P. Talkner, and M. Borkovec, Rev. Mod.
  Phys. 62, 251 (1990)], the di usion rate is proportional to exp ( F=k<sub>B</sub>T), with the free energy di erence F = E T S, where E is the energy barrier, and the prefactor arises from the transition entropy S. In the case studied here, the entropy is strongly temperature-dependent due to critical uctuations, which leads to an additional contribution to the e ective di usion barrier E<sup>A</sup><sub>A</sub> as obtained from an Arrhenius plot.
- [20] J.W .Hausand K.W .Kehr, Phys.Rep. 150, 263 (1987).
- [21] In this work, the crossover time n<sub>co</sub> was chosen to be the value of n, at which the relative deviation of logW (n) from its asymptotic form was half percent [18].



FIG.1. Results for D<sub>T</sub> and D<sub>C</sub> as a typical A mhenius plot in the O /W (110) system at = 0.45. We also show the behavior of the average transition rate and the therm odynam ic factor . The quantities D<sub>T</sub>, D<sub>C</sub>, and have been made dimensionless by expressing them in units of  $a^2 = t_0$ ,  $a^2 = t_0$ , and  $1 = t_0$ , respectively, where a is the lattice constant and  $t_0$  is one M onte C arlo step per particle. The value of , which is a dimensionless quantity, has been scaled by a factor of seven to make the graphic representation more readable while other quantities are expressed directly in the units given above. The critical tem perature of the order-disorder phase transition is denoted by T<sub>c</sub> and a dotted line.



FIG.2. Results for the elective activation barriers. The squares denote results based on the Arrhenius form (see Eq.(1)) for tracer di usion, while open circles represent the data based on the tail of W (n). Behavior of the prefactor D  $_0$  is illustrated in the inset. The critical tem perature is denoted by a dotted line.



FIG.3. An example of a waiting-time distribution W (n) at a temperature of 0.774 T<sub>c</sub> showing an exponential decay at long times. For clarity, only some of the data points are shown here. The full curve is an exponential to the tail of W (n). The approximate crossover time  $n_{co}$  for the crossover from the small-time regime to the asymptotic long-time regime [21] is indicated by an arrow.



FIG.4. Comparison of the short-time contribution  $hni_s$  and the long-time contribution  $hni_L$  to the average wait-ing-time hni. The slight increase of  $hni_L$  at small T is due to  $n_{co}$  whose value is di cult to determ ine accurately at very low temperatures. The quantities  $hni_s$ ,  $hni_L$ , and hni are all expressed in units of one M onte C arb step per particle.